

isc Silicon PNP Darlington Power Transistor

MJ4032

DESCRIPTION

- With TO-3 package
- Respectively complement to type MJ4035
- DARLINGTON
- High DC current gain

APPLICATIONS

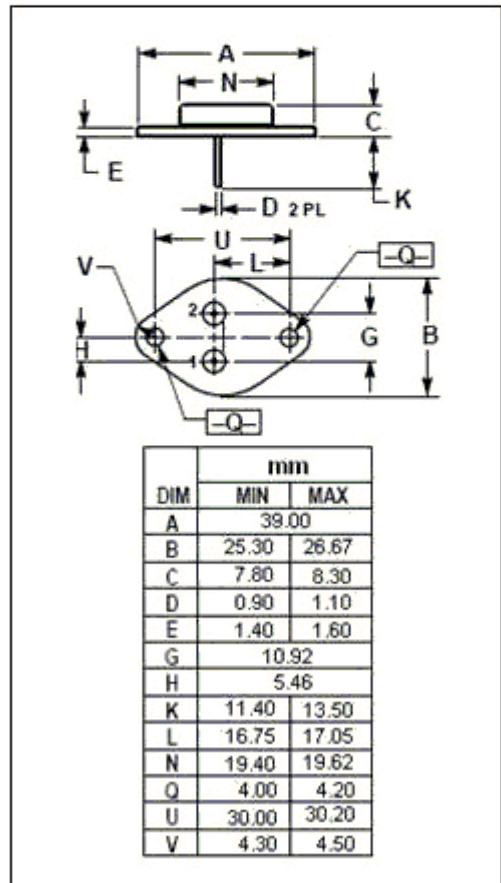
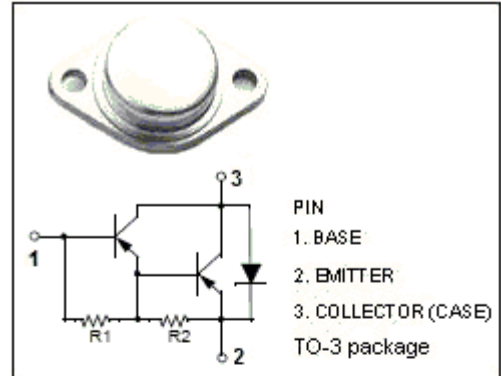
- For use as output devices in complementary general purpose amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_C=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-16	A
I_B	Base Current	-0.5	A
P_C	Collector Power Dissipation@ $T_C=25^\circ C$	150	W
T_J	Junction Temperature	200	$^\circ C$
T_{stg}	Storage Temperature	-55~200	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.17	$^\circ C/W$



isc Silicon PNP Darlington Power Transistor**MJ4032****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{CEO}	Collector-Emitter Breakdown Voltage	$I_C=-100\text{mA}; I_B=0$	-100		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=-10\text{A}; I_B=-40\text{mA}$		-2.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=-16\text{A}; I_B=-80\text{mA}$		-4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=-5\text{A}; I_B=-400\text{mA}$		-3	V
$V_{BE(on)}$	Base-Emitter On voltage	$I_C=-10\text{A}; V_{CE}=-3\text{V}$		-3	V
I_{CER}	Collector Cutoff Current	$V_{CB}=-100\text{V}; R_{BE}=1\text{K}\Omega$; $V_{CB}=-100\text{V}; R_{BE}=1\text{K}\Omega; T_C=150^{\circ}\text{C}$		-1 -5	mA
I_{CEO}	Collector Cutoff current	$V_{CE}=-50\text{V}; I_B=0$		-3	mA
I_{EBO}	Emitter Cut-off current	$V_{EB}=-5\text{V}; I_C=0$		-5	mA
h_{FE}	DC Current Gain	$I_C=-10\text{A}; V_{CE}=-3\text{V}$	1000		